

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-14. (Canceled)

15. (Currently Amended) A semiconductor device comprising:  
a semiconductor chip;  
a substrate on which a interconnecting pattern is formed; and  
a binder electrically connecting the semiconductor chip and the interconnecting pattern, the binder including:

a first-layer, layer including a first resin; and  
a second layer including conductive particles dispersed only in a second resin, the second layer being disposed closer to the substrate than the first layer, a coefficient of thermal expansion of the first layer-resin being smaller than a coefficient of thermal expansion of the second resin.

16. (Original) The semiconductor device as defined in Claim 15, wherein the binder is an anisotropic conductive film.

17-18. (Canceled)

19. (Previously Presented) A circuit board on which the semiconductor device as defined in Claim 15 is mounted.

20. (Presently Presented) Electronic equipment comprising the semiconductor device as defined in Claim 15.

21-28. (Canceled)

29. (Previously Presented) The semiconductor device as defined in Claim 15, wherein a silica insulating filler is mixed only in the first layer.

30. (Previously Presented) The semiconductor device as defined in Claim 15, wherein the second layer includes an epoxy resin.

31. (Previously Presented) The semiconductor device as defined in Claim 15, wherein conductive particles are dispersed only in the second layer.

32. (Previously Presented) The semiconductor device as defined in Claim 15, wherein the conductive particles are dispersed only in the second layer; and wherein the second layer is thinner than the first layer, and the second layer has higher viscosity than the first layer when melted.

33. (Currently Amended) The semiconductor device as defined in Claim 15, wherein a silica insulating filler is mixed only in the second-first layer.

34. (Currently Amended) The semiconductor device as defined in Claim 15, wherein a silica insulating filler is mixed in the first layer and the second layer, and a component ratio of the silica insulating filler in the second-first layer is greater than a component ratio of the silica insulating filler in the first-second layer.

35. (Currently Amended) The semiconductor device as defined in Claim 15, ~~wherein a molecular weight of the second layer is greater than a molecular weight of the first layer; at least the first resin including an epoxy resin.~~

36. (Currently Amended) A semiconductor device comprising:  
a semiconductor chip;  
a substrate on which a interconnecting pattern is formed; and  
a binder electrically connecting the semiconductor chip and the interconnecting pattern, the binder including:

~~a first-layer; layer including a first resin; and~~

a second layer including conductive particles dispersed only in a second resin,  
the second layer being disposed closer to the substrate than the first layer, wherein a modulus  
of elasticity of the second layer is resin being smaller than a modulus of elasticity of the first  
layer.resin.

37. (Previously Presented) The semiconductor device as defined in Claim 36,  
wherein the binder is an anisotropic conductive film.

38. (Previously Presented) The semiconductor device as defined in Claim 36,  
wherein a coefficient of thermal expansion of the first layer is smaller than a coefficient of  
thermal expansion of the second layer.

39. (Previously Presented) The semiconductor device as defined in Claim 36,  
wherein a silica insulating filler is mixed only in the first resin.

40. (Previously Presented) The semiconductor device as defined in Claim 36,  
wherein a silica insulating filler is mixed in the first layer and the second layer, and a  
component ratio of the silica insulating filler in the first layer is greater than a component ratio  
of the silica insulating filler in the second layer.

41. (Previously Presented) The semiconductor device as defined in Claim 36,  
wherein the second resin includes an epoxy resin.

42. (Previously Presented) The semiconductor device as defined in Claim 36,  
wherein conductive particles are dispersed only in the second layer; and  
wherein the second layer is thinner than the first layer, and the second layer has  
higher viscosity than the first layer when melted.

43. (Currently Amended) The semiconductor device as defined in Claim 36,  
wherein a molecular weight of the second layer is greater than a molecular weight of the first  
layer.the first resin including an epoxy resin and the second resin including a biphenyl resin.

44. (Previously Presented) A circuit board on which the semiconductor device as defined in Claim 36 is mounted.

45. (Previously Presented) Electronic equipment comprising the semiconductor device as defined in Claim 36.

46-49. (Canceled)